IN THE CLAIMS:

Please cancel claims 3 and 8 without prejudice.

1. (Previously Presented) A method for improving metal deposition on a patterned dielectric layer, comprising:

a) cleaning the patterned dielectric layer in a processing chamber with a first plasma consisting essentially of argon;

b) cleaning the patterned dielectric layer in the processing chamber with a second plasma consisting essentially of hydrogen and helium after cleaning the patterned dielectric layer with the first plasma; and

c) depositing a metal on the patterned dielectric layer after exposing the dielectric layer to the first plasma and the second plasma.

2-3. (Canceled)

4. (Previously Presented) The method of claim 1, wherein the second plasma consists essentially of about 5% hydrogen by number of atoms and about 95% helium by number of atoms.

5. (Canceled)

6. (Previously Presented) A method for improving metal deposition on a patterned dielectric layer on a substrate, comprising:

a) cleaning the patterned dielectric layer in a processing chamber with a first plasma consisting essentially of argon, wherein the first plasma is generated by supplying a RF power to a coil surrounding the processing chamber and supplying a RF power to bias a substrate support member supporting the substrate;

b) cleaning the patterned dielectric layer in the processing chamber with a second plasma consisting essentially of hydrogen and helium after cleaning the

patterned dielectric layer with the first plasma, wherein the second plasma is generated by supplying the RF power to the coil surrounding the processing chamber and supplying the RF power to bias the substrate support member supporting the substrate; and

c) depositing a metal layer after exposing the dielectric layer to the first plasma and the second plasma.

7-8. (Canceled)

9. (Previously Presented) The method of claim 6, wherein the second plasma consists essentially of about 5% hydrogen by number of atoms and about 95% helium by number of atoms.

10. (Previously Presented) The method of claim 6, further comprising depositing a barrier layer prior to depositing the metal layer.

11. (Previously Presented) The method of claim 6, wherein the RF power supplied to bias the substrate support member and generate the second plasma is less than the RF power supplied to bias the substrate support member and generate the first plasma.

12. (Previously Presented) The method of claim 6, wherein the first plasma is generated with about 300 W of the RF power supplied to the coil and about 300 W of the RF power supplied to bias the substrate support member, and the second plasma is generated with about 450 W of the RF power supplied to the coil and about 10 W of the RF power supplied to bias the substrate support member.

13. (Previously Presented) The method of claim 6, wherein each of the first plasma and the second plasma are maintained in the processing chamber for about 60 seconds.

14. (Previously Presented) A method for improving metal deposition on a patterned dielectric layer on a substrate, comprising:

a) cleaning the patterned dielectric layer in a processing chamber with a first plasma consisting essentially of argon, wherein the first plasma is generated by supplying a RF power to a coil surrounding the processing chamber and supplying a RF power to bias a substrate support member supporting the substrate;

b) cleaning the patterned dielectric layer in the processing chamber with a second plasma consisting essentially of hydrogen and helium after cleaning the patterned dielectric layer with the first plasma, wherein the second plasma is generated by increasing the supply of the RF power to the coil surrounding the processing chamber and reducing the supply of the RF power to bias the substrate support member supporting the substrate;

c) depositing a barrier layer on the patterned dielectric layer after exposing the dielectric layer to the first plasma and the second plasma; and

d) depositing a metal on the barrier layer.

15-16. (Canceled)

17. (Original) The method of claim 14, wherein the second plasma consists essentially of about 5% of hydrogen by number of atoms and about 95% of helium by number of atoms.

18. (Previously Presented) The method of claim 14, wherein the first plasma is generated with about 300 W of the RF power supplied to the coil and about 300 W of the RF power supplied to bias the substrate support member, and the second plasma is generated with about 450 W of the RF power supplied to the coil and about 10 W of the RF power supplied to bias the substrate support member.

19. (Previously Presented) The method of claim 14, wherein each of the first plasma and the second plasma are maintained in the processing chamber for about 60 seconds.

20. (Previously Presented) The method of claim 14, wherein the first plasma is generated at about 0.8 mtorr, and the second plasma is generated at about 80 mtorr.

21. (Original) The method of claim 1, wherein the patterned dielectric layer comprises one or more features having an aspect ratio greater than 1:1.

22. (Original) The method of claim 6, wherein the patterned dielectric layer comprises one or more features having an aspect ratio greater than 1:1.

23. (Original) The method of claim 14, wherein the patterned dielectric layer comprises one or more features having an aspect ratio greater than 1:1.

24-32. (Canceled)

33. (Previously Presented) A method for improving metal deposition on a patterned dielectric layer, comprising:

a) patterning a dielectric layer in a processing chamber to form one or more features having an aspect ratio greater than 1:1;

b) cleaning the patterned dielectric layer in the processing chamber with a first plasma consisting essentially of argon;

c) cleaning the patterned dielectric layer in the processing chamber with a second plasma comprising about 5% hydrogen by number of atoms and 95% helium by number of atoms after cleaning the patterned dielectric layer with the first plasma; and

d) depositing a metal on the patterned dielectric layer after exposing the dielectric layer to the first plasma and the second plasma.